

Page 11, lines 28 and 29, strike "filed on the same day as the present application," and substitute the following therefore: --Serial No. 07/337,579, filed April 13, 1989, now abandoned,--.

Page 22, line 14, insert after "204,175" --now patent no. 5,095,344,--.

Page 22, line 16, change "Techniques." to Techniques, Serial No. 07/337,579, filed

A3 April 13, 1989, now abandoned.

Page 26, line 3, insert a comma --,-- after "204,175" and insert thereafter --now patent no. 5,095,344,--.

Page 26, strike all of line 4, and substitute the following therefore: Harari, Serial No. 07/337,579, filed April 13, 1989, now abandoned,--.

IN THE CLAIMS:

Cancel claims 1-62, without prejudice, and substitute the following new claims 63-67 therefor:

--63. A semiconductor memory selectively enabled for operation as a complete operative memory or a partial operative memory, comprising:

a plurality of memory arrays, each memory array comprising a plurality of memory blocks; and

a plurality of selection circuits respectively associated with said plurality of memory arrays, selectively and independently disabling a defective memory block and selecting a normal memory block of a memory array for enabling operation thereof as a partial operative memory.

64. A semiconductor memory as claimed in claim 63, wherein each of said memory arrays comprises a first memory block and a second memory block, and said respective selection circuit disables said first memory block and selects said second memory block, when said first memory block is defective and said second memory block is normal.

65. A semiconductor memory as claimed in claim 63, wherein each said selection circuit disables a defective memory block and selects a normal memory block in accordance with specific signals.

66. A semiconductor memory selectively enabled for operation as a complete operative memory or a half operative memory, comprising:

a plurality of memory arrays, each memory array comprising a first memory block and a second memory block; and